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SUPPLEMENTAL INFORMATION	:	Applicant: Berger
DISCLOSURE STATEMENT	:	Group Art Unit: 2811
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**OTHER DOCUMENTS**

1. Amlani, I. et al., Digital Logic Gate Using Quantum-Dot Cellular Automata, *Science*, 284, pp. 289-291 (April 9, 1999).
2. Fay, P. et al., Integration of InAs/AlSb/GaSb Resonant Interband Tunneling Diodes with Heterostructure Field-Effect Transistors for Ultra-High-Speed Digital Circuit Applications, *IEEE*, pp. 162-165 (1999).
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5. Nayak, D. et al., Rapid Thermal Oxidation of GeSi Strained Layers, *Appl. Phys. Lett.*, 56, pp. 66-68 (January 1, 1990).

Examiner <b>CRANE</b>	Date Considered <b>8/2005</b>
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**U.S. PATENT DOCUMENTS**

Examiner's Initial	Document Number	Date	Name	Class/Sub- class
	NONE			

**FOREIGN PATENT DOCUMENTS**

Examiner's Initial	Document Number	Date	Country/Name	Translation yes/no
	NONE			

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2. Amlani, I. et al., Demonstration of a six-dot quantum cellular automata system, *Applied Physics Letters*, 72, pp. 2179-2181 (1998).
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